

Q2 -- Then upon the entire surface including the lower electrode 50, there are sequentially deposited a dielectric medium 51 and an upper electrode 52. The dielectric medium 51 also covers the remaining portion of the seed separating layer 45 not covered by the seed layer 46.--

Please replace the paragraph beginning on page 11, line 21, with the following rewritten paragraph:

Q3 -- As shown in the drawing, the completed semiconductor device includes: a connecting part 44 connected through an insulating layer 43 of a substrate 41 to a conductive layer 42; a seed separating layer 45 formed around the connecting part 44 and the insulating layer 43 to open at least the connecting part 44; a seed layer 46 filled into the open part of the seed separating layer 45 and covering an inner portion of the seed separating layer 45; and a capacitor consisting of: a lower electrode 50 formed upon the seed layer 46, a dielectric medium 51 formed upon the lower electrode 50 and the remaining portion of the seed separating layer 45 not covered by the seed layer 46, and an upper electrode 52 formed upon the dielectric medium 51.--

In the Claims:

Please amend claim 1, as follows:

- Q4 1. (Amended) A semiconductor device comprising:
- a substrate coated with an insulating layer;
 - a connecting part connected to a conductive layer through the insulating layer of the substrate;
 - a seed separating layer formed around the connecting part and the insulating layer, the seed separating layer defining an open region that exposes at least part of the connecting part;
 - a seed layer disposed in the open region of the seed separating layer and covering a first portion of the seed separating layer; and
 - a capacitor comprising a lower electrode formed on the seed layer, a dielectric medium formed on the lower electrode and further covering a second portion of the seed separating layer, and an upper electrode formed on the dielectric medium.

Please cancel claims 13-20, without prejudice or disclaimer.